

UNISONIC TECHNOLOGIES CO., LTD

UTT100N08 Preliminary Power MOSFET

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

■ DESCRIPTION

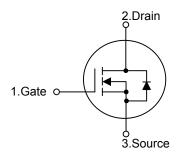
The UTC **UTT100N08** is an N-channel enhancement mode Power FET using UTC's advanced technology to provide customers with a minimum on-state resistance and superior switching performance.

It also can withstand high energy pulse in the avalanche and commutation mode.

■ FEATURES

- * Fast switching speed
- * $R_{DS(ON)}$ = 7m Ω @ V_{GS} =10V
- * Work below 175°C
- * 100% avalanche tested
- * Improved dv/dt capability

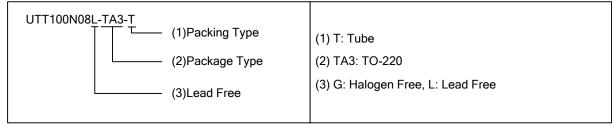
■ SYMBOL

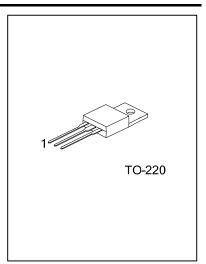


ORDERING INFORMATION

Ordering Number		Doolsono	Pin Assignment			Daakina	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTT100N08L-TA3-T	UTT100N08G-TA3-T	TO-220	G	D	S	Tube	

Note: Pin Assignment: G: Gate D: Drain S: Source





■ ABSOLUTE MAXIMUM RATINGS (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	80	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous	I_D	100	Α
	Pulsed	I _{DM}	400	Α
Avalanche Energy	Single Pulsed	E _{AS}	875	mJ
Peak Diode Recovery dv/dt		dv/dt	6	V/ns
Power Dissipation		P _D	83	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T _{STG}	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	θ_{JA}	62.5	°C/W	
Junction to Case	θ_{JC}	1.5	°C/W	

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS			•			
Drain-Source Breakdown Voltage	BV _{DSS}	$I_D=250\mu A, V_{GS}=0V$	80			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			10	μΑ
Cata Source Leakage Current Forward		V_{GS} =+20V, V_{DS} =0V			+100	nA
Gate- Source Leakage Current Reverse	I_{GSS}	V _{GS} =-20V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu A$	1		3	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =10V, I_D =50A		7	12	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}			1500		pF
Output Capacitance	Coss	V_{GS} =0V, V_{DS} =25V, f=1.0MHz		1060		pF
Reverse Transfer Capacitance	C _{RSS}			700		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G			500		nC
Gate to Source Charge	Q_GS	V_{GS} =10V, V_{DS} =30V, I_{D} =100A		50		nC
Gate to Drain Charge	Q_GD			33		nC
Turn-ON Delay Time	t _{D(ON)}			90		ns
Rise Time	t _R	V _{DD} =30V, VGS=10V,		130	200	ns
Turn-OFF Delay Time	t _{D(OFF)}	$I_D = 100A, R_G = 0.4\Omega$		768		ns
Fall-Time	t _F			280	420	ns
Transconductance	g fs	V _{DS} =15V, I _D =30A	30			S
SOURCE- DRAIN DIODE RATINGS AND	CHARACTER	ISTICS				
Maximum Body-Diode Continuous Current	Is		100			Α
Maximum Body-Diode Pulsed Current	I _{SM}		400			Α
Drain-Source Diode Forward Voltage	V _{SD}	I _S =100A, V _{GS} =0V		1.0	1.5	V
Resistance of Gate	R _G		0.65	1.3	2	Ω

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